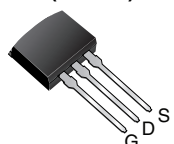


Power MOSFET

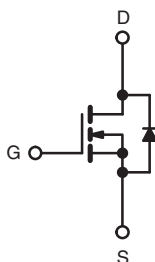
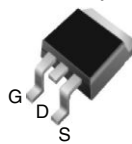
PRODUCT SUMMARY

V_{DS} (V)	60	
$R_{DS(on)}$ (Ω)	$V_{GS} = 10\text{ V}$	0.018
Q_g (Max.) (nC)	110	
Q_{gs} (nC)	29	
Q_{gd} (nC)	36	
Configuration	Single	

I²PAK (TO-262)



D²PAK (TO-263)



N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21

Definition

- Advanced Process Technology
- Dynamic dV/dt
- 175 °C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Drop in Replacement of the IRFZ48, SiHFZ48 for Linear/Audio Applications
- Compliant to RoHS Directive 2002/95/EC



RoHS*
COMPLIANT
HALOGEN
FREE
Available

DESCRIPTION

Advanced Power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²PAK is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2 W in a typical surface mount application.

ORDERING INFORMATION

Package	D ² PAK (TO-263)	I ² PAK (TO-262)
Lead (Pb)-free and Halogen-free	SiHFZ48RS-GE3	-
Lead (Pb)-free	IRFZ48RSPbF SiHFZ48RS-E3	IRFZ48RLPbF SiHFZ48RL-E3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^e	I_D	$T_C = 25\text{ °C}$	A
		$T_C = 100\text{ °C}$	
Pulsed Drain Current ^{a, e}	I_{DM}	290	
Linear Derating Factor		1.3	W/°C
Single Pulse Avalanche Energy ^{b, e}	E_{AS}	100	mJ
Maximum Power Dissipation	P_D	190	W
Peak Diode Recovery dV/dt ^{c, e}	dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 175	°C
Soldering Recommendations (Peak Temperature) ^d	for 10 s	300 ^d	
Mounting Torque	6-32 or M3 screw	10	lbf · in
		1.1	N · m

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25\text{ V}$, Starting $T_J = 25\text{ °C}$, $L = 22\text{ }\mu\text{H}$, $R_g = 25\text{ }\Omega$, $I_{AS} = 72\text{ A}$ (see fig. 12).
- $I_{SD} \leq 72\text{ A}$, $dI/dt \leq 200\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 175\text{ °C}$.
- 1.6 mm from case.
- Current limited by the package, (die current = 72 A).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.8	

SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		60	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 1 mA ^c		-	0.60	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2.0	-	4.0	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V		-	-	25	μA
		V _{DS} = 48 V, V _{GS} = 0 V, T _J = 150 °C		-	-	250	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 43 A ^b	-	-	0.018	Ω
Forward Transconductance	g _{fs}	V _{DS} = 25 V, I _D = 43 A ^b		27	-	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1.0 MHz, see fig. 5 ^c		-	2400	-	pF
Output Capacitance	C _{oss}			-	1300	-	
Reverse Transfer Capacitance	C _{rss}			-	190	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 72 A, V _{DS} = 48 V, see fig. 6 and 13 ^{b, c}	-	-	110	nC
Gate-Source Charge	Q _{gs}			-	-	29	
Gate-Drain Charge	Q _{gd}			-	-	36	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 30 V, I _D = 72 A, R _g = 9.1 Ω, R _D = 0.34 Ω, see fig. 10 ^{b, c}		-	8.1	-	ns
Rise Time	t _r			-	250	-	
Turn-Off Delay Time	t _{d(off)}			-	210	-	
Fall Time	t _f			-	250	-	
Internal Drain Inductance	L _D	Between lead, 6 mm (0.25") from package and center of die contact		-	4.5	-	nH
Internal Source Inductance	L _S			-	7.5	-	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50 ^c	A
Pulsed Diode Forward Current ^a	I _{SM}			-	-	290	
Body Diode Voltage	V _{SD}	T _J = 25 °C, I _S = 72 A, V _{GS} = 0 V ^b		-	-	2.0	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = 72 A, dI/dt = 100 A/μs ^{b, c}		-	120	180	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	0.50	0.80	μC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L _S and L _D)					

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- Current limited by the package, (die current = 72 A).



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

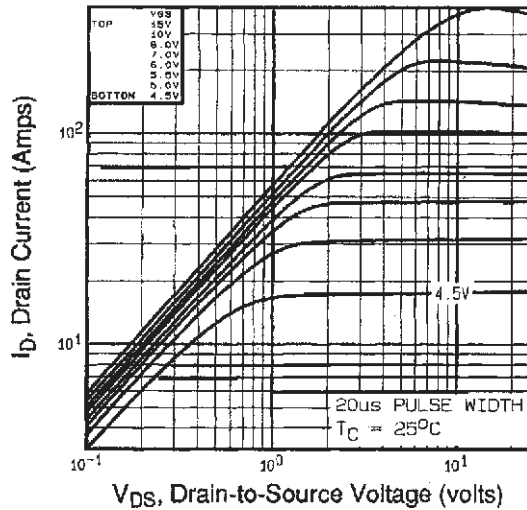


Fig. 1 - Typical Output Characteristics

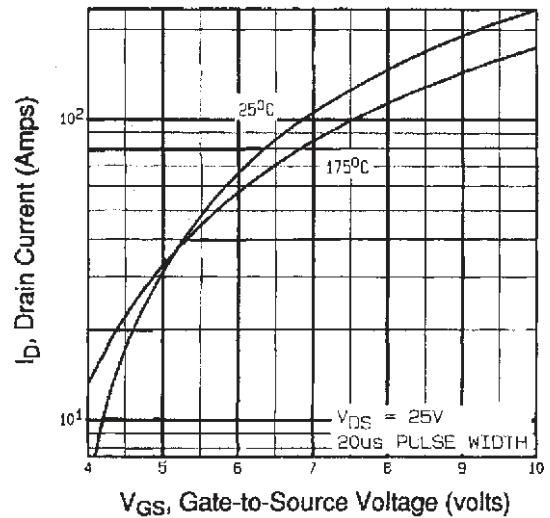


Fig. 3 - Typical Transfer Characteristics

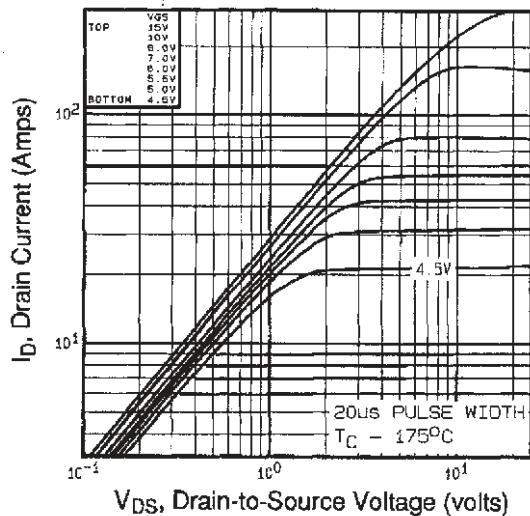


Fig. 2 - Typical Output Characteristics

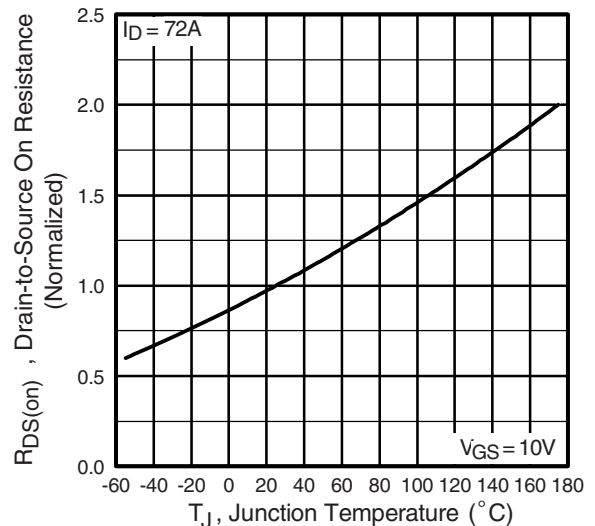


Fig. 4 - Normalized On-Resistance vs. Temperature

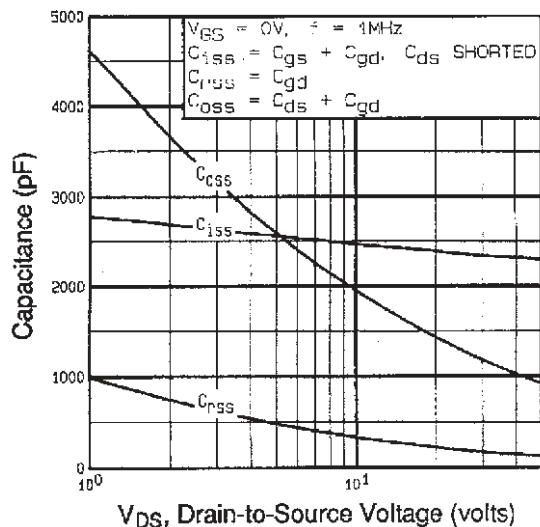


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

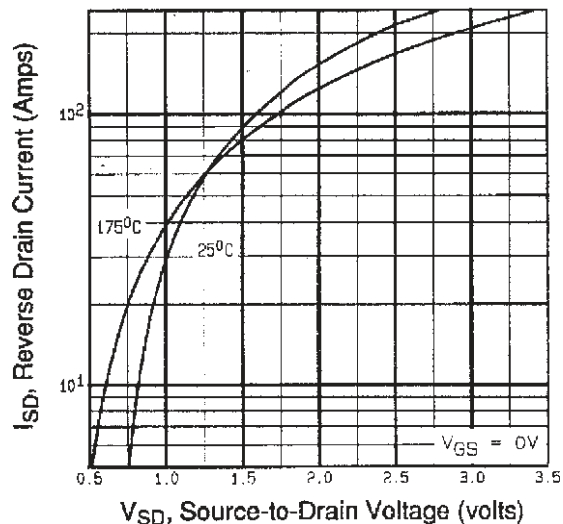


Fig. 7 - Typical Source-Drain Diode Forward Voltage

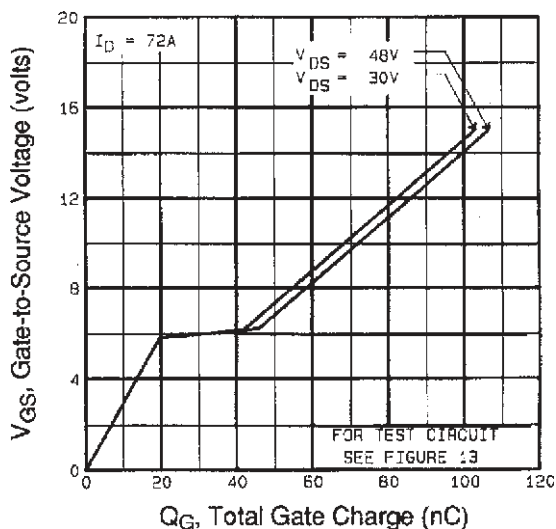


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

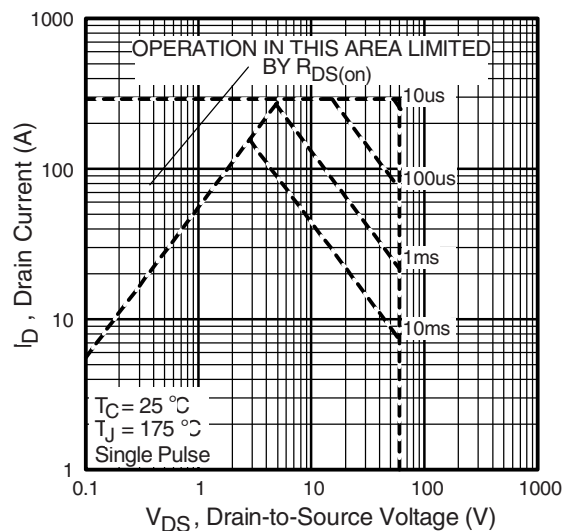


Fig. 8 - Maximum Safe Operating Area

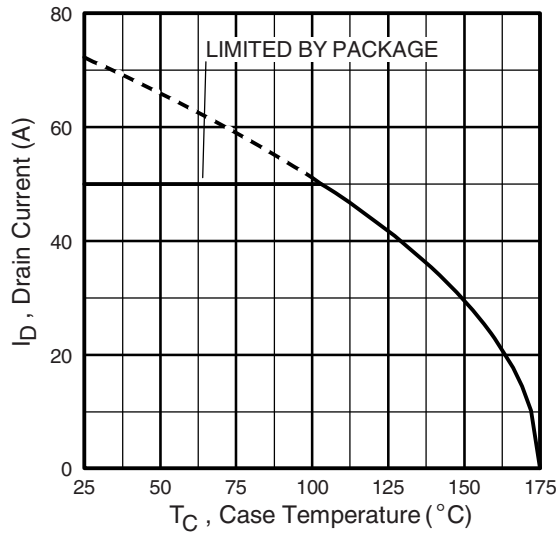


Fig. 9 - Maximum Drain Current vs. Case Temperature

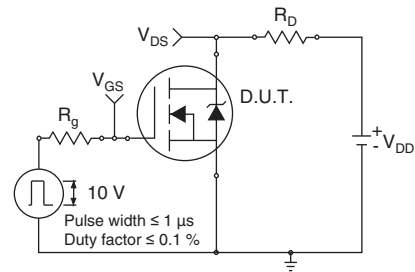


Fig. 10a - Switching Time Test Circuit

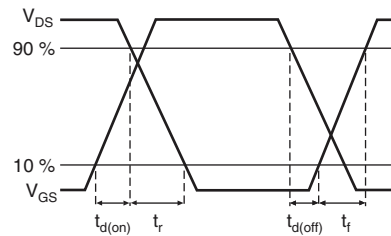


Fig. 10b - Switching Time Waveforms

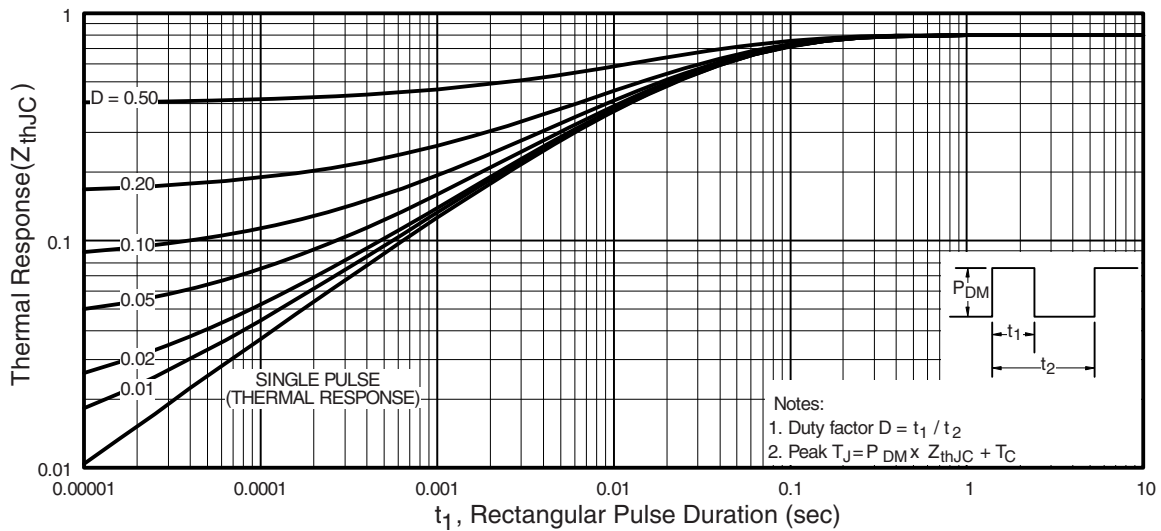


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

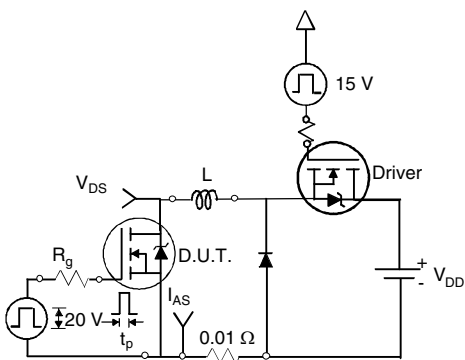


Fig. 12a - Unclamped Inductive Test Circuit

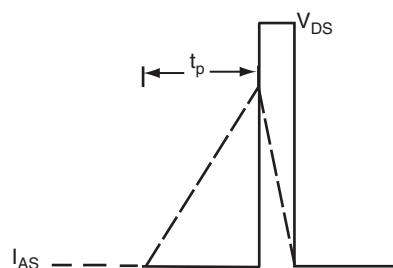


Fig. 12b - Unclamped Inductive Waveforms

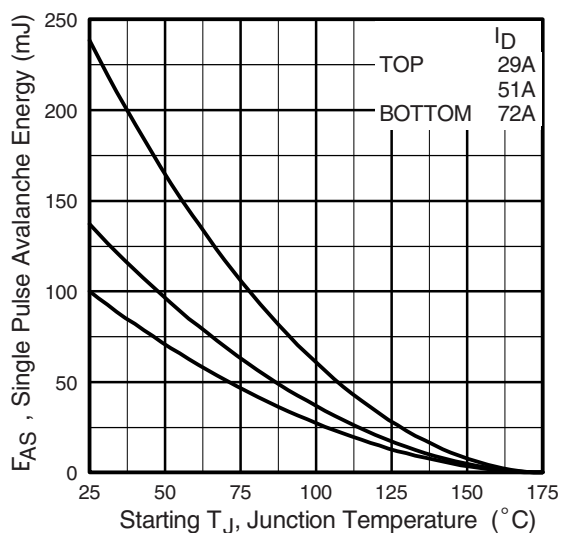


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

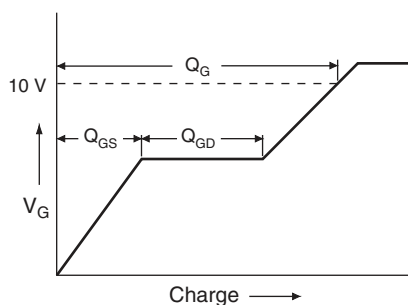


Fig. 13a - Maximum Avalanche Energy vs. Drain Current

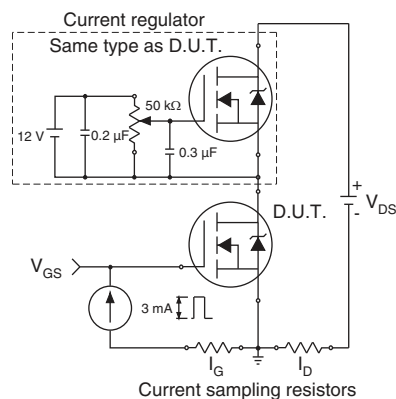
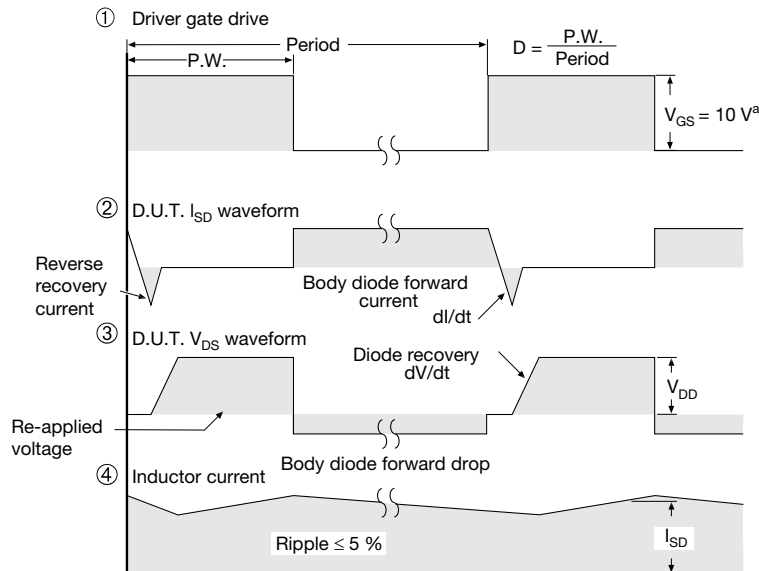
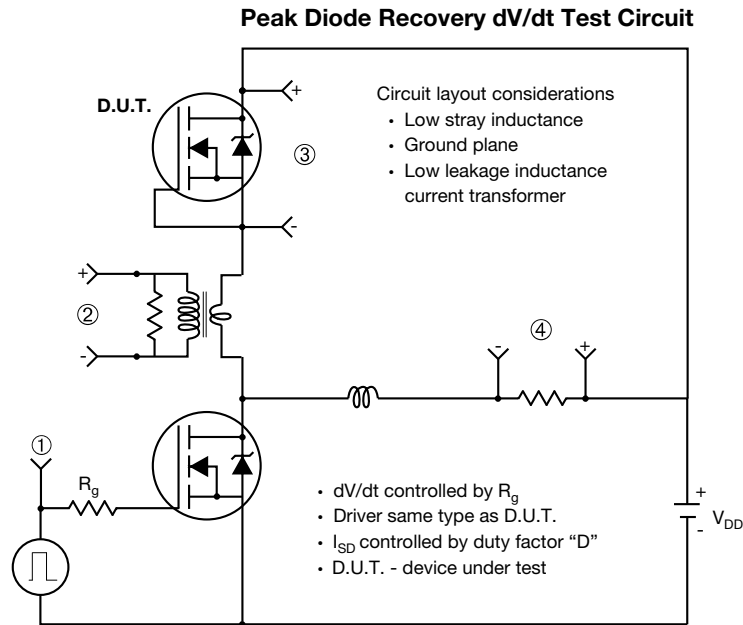


Fig. 13b - Gate Charge Test Circuit



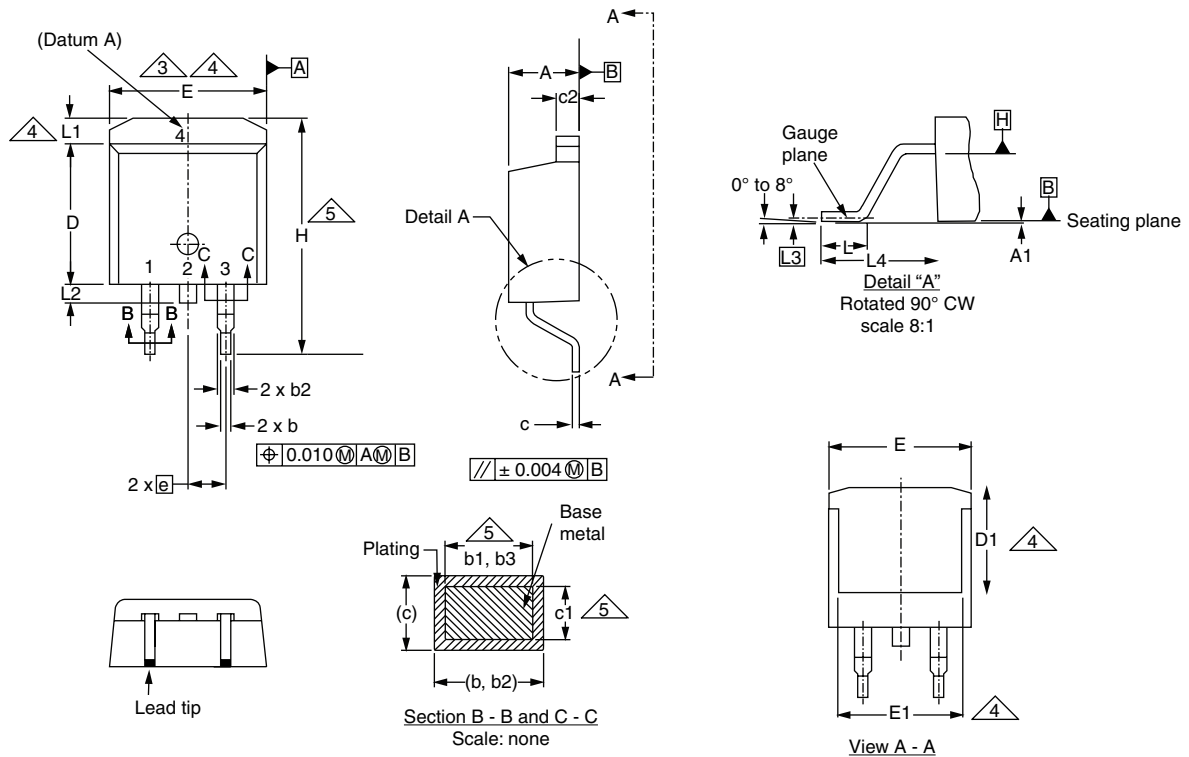
Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

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TO-263AB (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

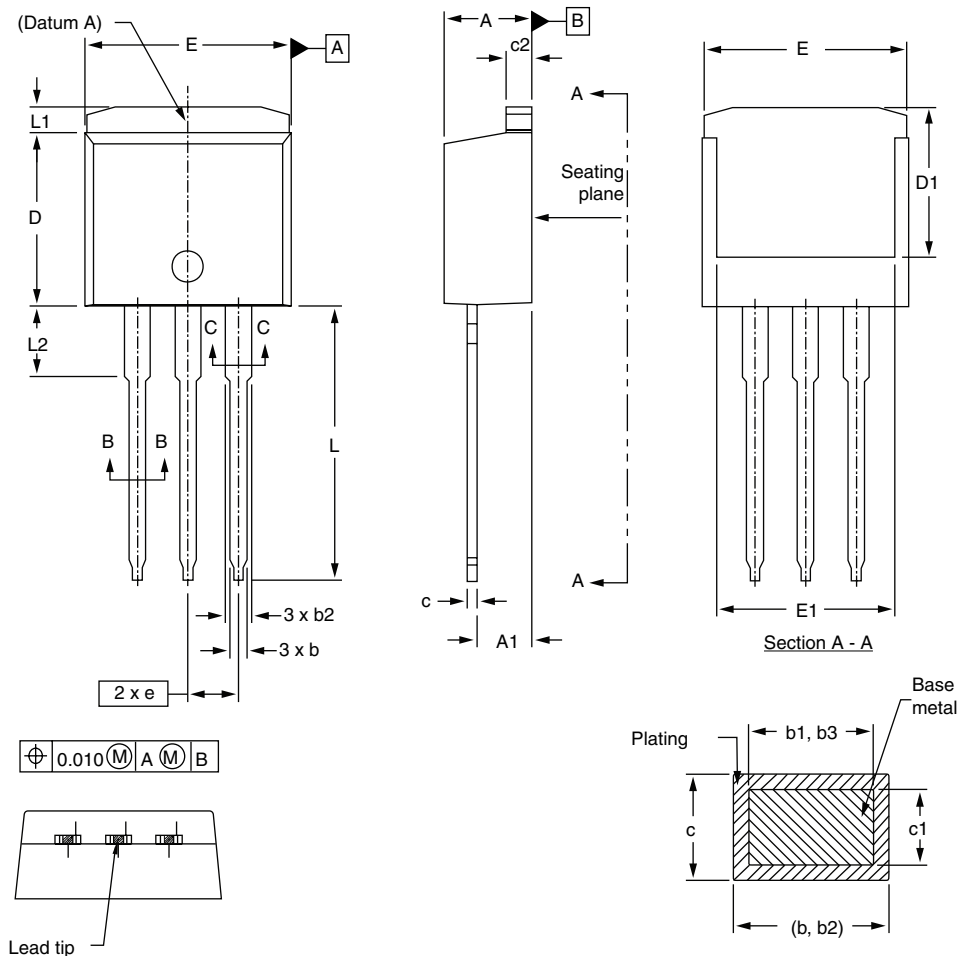
DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

ECN: S-82110-Rev. A, 15-Sep-08
DWG: 5970

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimensions are shown in millimeters (inches).
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
5. Dimension b1 and c1 apply to base metal only.
6. Datum A and B to be determined at datum plane H.
7. Outline conforms to JEDEC outline to TO-263AB.

I²PAK (TO-262) (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

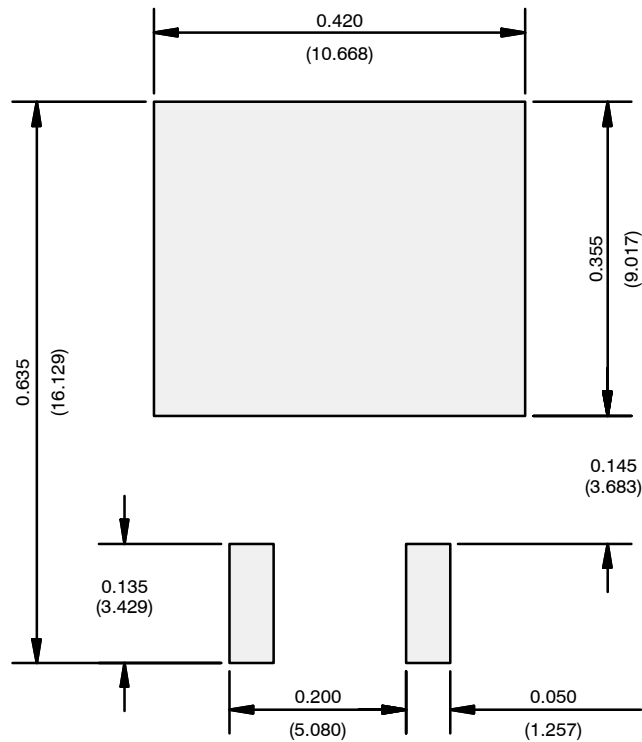
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

ECN: S-82442-Rev. A, 27-Oct-08
DWG: 5977

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

[Return to Index](#)



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